Abstracts

A 2--18-GHz Monolithic Distributed Amplifier Using Dual-Gate GaAs FET's

W. Kennan, T. Andrade and C.C. Huang. "A 2--18-GHz Monolithic Distributed Amplifier Using Dual-Gate GaAs FET's." 1984 Transactions on Microwave Theory and Techniques 32.12 (Dec. 1984 [T-MTT] (1984 Symposium Issue)): 1693-1698.

This paper describes a 2--18-GHz monolithic distributed amplifier with over 6-dB gain, ± 0.5-dB gain flatness, and less than 2.0:1 VSWR. Measured noise figure is below 7.5 dB, and power output capability is greater than 17 dBm. The amplifier is designed with dual-gate GaAs FET's instead of single-gate FET's for maximum gain over the design bandwidth. Cascaded amplifier performance will also be presented.

❑ Return to main document.